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**INFORMATION DISCLOSURE  
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Date Submitted: November 3, 2005

(use as many sheets as necessary)

1 of 1

**Complete if Known**

Application Number	10/755,602
Filing Date	01/12/2004
First Named Inventor	Qi Xiang
Group Art Unit	2813
Examiner Name	Jack Chen
Attorney Docket Number	039153-0693 (H1718)

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
	A1	2004/0142537	A1	Lee et al.	07-22-2004	
	A2	2004/0135138	A1	Hsu et al.	07-15-2004	
	A3	2004/0132267	A1	Sadana et al.	07-08-2004	
	A4	2004/0036142	A1	Shima	02-26-2004	
	A5	6,673,698	B1	Arasnia et al.	01-08-2004	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Office <sup>4</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
	A6	WO	2004/061920	A3	Wang et al.	07-22-2004		
	A7	WO	2004/061920	A2	Wang et al.	07-22-2004		
	A8	WO	2003/094208	A3	O'Neill	11-13-2003		
	A9	WO	03/094208	A2	O'Neill	11-13-2003		

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
	A10	TAKAGI, S. ET AL., "Device structure and electrical characteristics of strained-Si-on-insulator (strained-SOI) MOSFETs," Materials Science and Engineering, 2002, pages 428-434, B89, Elsevier.	
	A11	TAKAGI, SHIN-ICHI ET AL., "Strained SOI Technology for High-Performance, Low-Power CMOS Applications," 2003 IEEE International Solid-State Circuits Conference, February 12, 2003, 9 pages, 0-7803-7707-9/03.	
	A12	International Search Report and Written Opinion for Application No. PCT/US2004/043107, date of mailing 04/10/2005, 17 pages.	

Examiner Signature

*[Handwritten Signature]*

Date Considered

3/31/06

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<sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 18 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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